DISCRETE SEMICONDUCTORS

DATA SHEET

PEMB9; **PUMB9** PNP/PNP resistor-equipped transistors; R1 = 10 kΩ, R2 = 47 kΩ

Product data sheet Supersedes data of 2003 Feb 03

2003 Oct 03



PNP/PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 47 k Ω

PEMB9; PUMB9

TYP. MAX. UNIT

kΩ

 $k\Omega$

FEATURES

- · Built-in bias resistors
- · Simplified circuit design
- · Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- · Low current peripheral drivers
- Replacement of general purpose transistors in digital applications
- · Control of IC inputs.

V _{CEO}	collector-emitter voltage	_	-50	V
Io	output current (DC)	_	-100	mA
TR1	PNP	_	-	_
TR2	PNP	_	_	_

10

47

PARAMETER

bias resistor

bias resistor

QUICK REFERENCE DATA

SYMBOL

R1

R2

DESCRIPTION

PNP/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE(1)	NPN/PNP	NPN/NPN	
TIPE NOWIBER	PHILIPS	EIAJ	MARKING CODE	COMPLEMENT	COMPLEMENT	
PEMB9	SOT666	_	Z6	PEMD9	PEMH9	
PUMB9	SOT363	SC-88	B*9	PUMD9	PUMH9	

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
TIPE NUMBER	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION
PEMB9	6 5 4	1	emitter TR1
PUMB9	6 5 4	2	base TR1
	R1 R2	3	collector TR2
	TR2	4	emitter TR2
	TR1 R2 R1	5	base TR2
		6	collector TR1
	1 2 3		
	1 2 3 Top view MAM477		
	. 55		

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ORDERING INFORMATION

TYPE NUMBER		PACKAGE			
TIPE NOMBER	NAME	DESCRIPTION	VERSION		
PEMB9	_	plastic surface mounted package; 6 leads	SOT666		
PUMB9	 plastic surface mounted package; 6 leads SOT363 		SOT363		

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transis	stor		<u>'</u>	•	
V_{CBO}	collector-base voltage	open emitter	_	-50	V
V_{CEO}	collector-emitter voltage	open base	_	-50	V
V _{EBO}	emitter-base voltage	open collector	_	-10	V
VI	input voltage				
	positive		_	+6	V
	negative		_	-40	V
I _O	output current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT363	note 1	_	200	mW
	SOT666	notes 1 and 2	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
Per device	•	•			
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT363	note 1	_	300	mW
	SOT666	notes 1 and 2	_	300	mW

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Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	note 1	416	K/W

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	_	_	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_B = 0; T_j = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0$	_	_	-150	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	100	_	_	
V _{CEsat}	saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	_	_	-100	mV
$V_{i(off)}$	input-off voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	_	-0.7	-0.5	V
$V_{i(on)}$	input-on voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -1 \text{ mA}$	-1.4	-0.8	_	V
R1	input resistor		7	10	13	kΩ
<u>R2</u> R1	resistor ratio		3.7	4.7	5.7	
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	_	_	3	pF

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PROJECTION

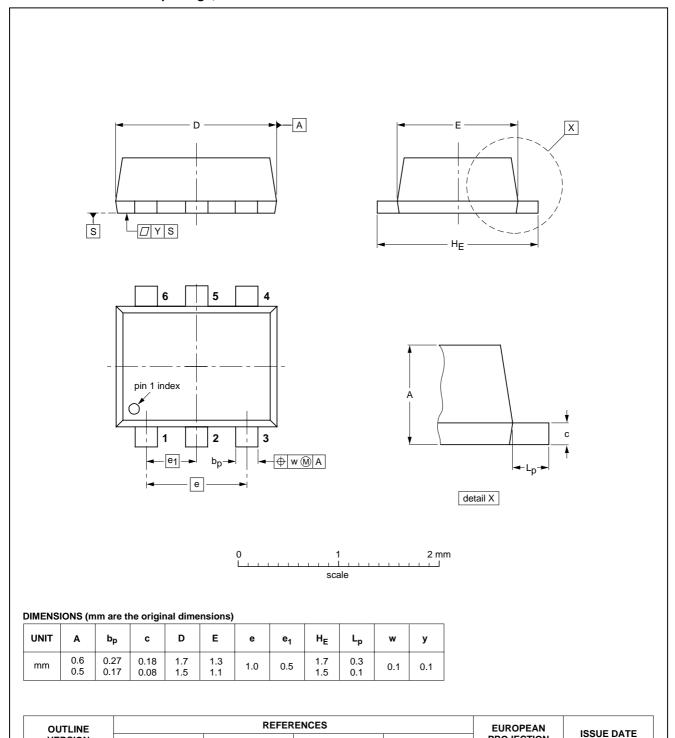
-01-01-04

01-08-27

PACKAGE OUTLINES

Plastic surface mounted package; 6 leads

SOT666



EIAJ

2003 Oct 03 5

IEC

JEDEC

VERSION

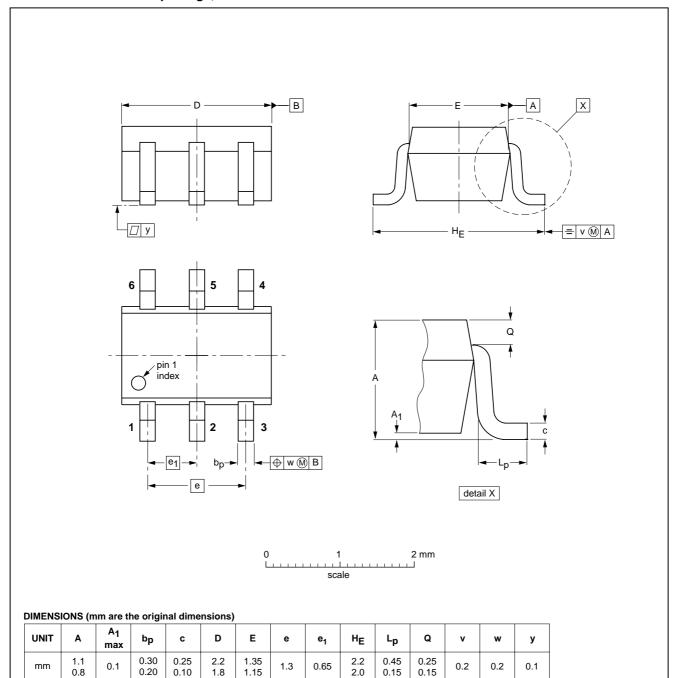
SOT666

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Plastic surface mounted package; 6 leads

SOT363



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION 1550E DA	
SOT363			SC-88		$ \ \ \bigoplus \big($	97-02-28

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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